

IRW

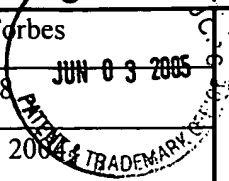


First Named Inventor	Leonard Forbes	GENERAL TRANSMITTAL FORM UNDER 37 CFR 1.8 (LARGE ENTITY)
Serial No.	10/808,058	
Filing Date	March 24, 2004	
Group Art Unit	2818	
Examiner Name	Unknown	
Confirmation No.	4217	
Attorney Docket No.	400.288US01	
Title: MEMORY DEVICE WITH HIGH DIELECTRIC CONSTANT GATE DIELECTRICS AND METAL FLOATING GATES		

Mail Stop: AMENDMENT
 Commissioner for Patents
 P. O. Box 1450
 Alexandria, VA 22313-1450

Enclosures					
The following documents are enclosed:					
<input checked="" type="checkbox"/>	Supplemental Information Disclosure Statement (1 pg.); Form 1449 (1 pg.); 4 copies of cited references; U.S. reference(s) not included pursuant to 37 C.F.R. 1.98 (c)(2)(i);				
<input checked="" type="checkbox"/>	An itemized return-receipt postcard				
Leffert Jay & Polglaze, P.A. P.O. Box 581009 Minneapolis, MN 55458-1009 T – 612/312-2200 F – 612/312-2250					
Please charge any additional fees or credit any overpayments to Deposit Account No. 501373.					
CUSTOMER NO. 27073					
Submitted By					
Name	Kenneth W. Bolvin	Reg. No.	34,125	Telephone	(612) 312-2211
Signature	<i>Kenneth W. Bolvin</i>			Date	5/3/05
Certificate of Mailing					
I certify that this correspondence and the identified documents listed on this transmittal are being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Mail Stop: AMENDMENT, Commissioner for Patents, P. O. Box 1450, Alexandria, VA 22313-1450 on May 31, 2005.					
Name	Kristen A. Smith		Signature	<i>Kristen Smith</i>	

(LARGE ENTITY TRANSMITTAL UNDER 37 CFR § 1.8)

First Named Inventor	Leonard Forbes		SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT
Serial No.	10/808,058		
Filing Date	March 24, 2004		
Group Art Unit	2818		
Examiner Name	Unknown		
Confirmation No.	4217		
Attorney Docket No.	400.288US01		
Title: MEMORY DEVICE WITH HIGH DIELECTRIC CONSTANT GATE DIELECTRICS AND METAL FLOATING GATES			

Mail Stop: AMENDMENT
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

In compliance with 37 C.F.R. §§ 1.56 and 1.97, *et seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified Application. Pursuant to 37 C.F.R. 1.98 (a)(2)(i), as this application was filed after June 30, 2003, Applicant has not included copies of U.S. Patents or U.S. Patent Applications. Applicant respectfully requests that this Supplemental Information Disclosure Statement be entered and the references listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to MPEP §609, Applicant further requests that the Examiner initial next to each reference on the Form 1449 to indicate that the listed references have been considered. Applicant further requests that a copy of the initialed Form 1449 be returned with the next official communication.

As an Office Action has not yet issued in this application, Applicant believes that no fees are due. However, the Commissioner for Patents is hereby authorized to charge any additional fees to Deposit Account No. 501373.

If the Examiner has any questions or concerns regarding this application, please contact the undersigned at (612) 312-2211.

Respectfully submitted,

Date: _____

5/31/05

Kenneth W. Bolvin

Kenneth W. Bolvin
Reg. No. 34,125

Attorneys for Applicant
Leffert Jay & Polglaze
P.O. Box 581009
Minneapolis, MN 55458-1009
T 612 312-2200
F 612 312-2250

First Named Inventor	Leonard Forbes	<p style="text-align: center;">SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT FORM PTO-1449</p>
Serial No.	10/808,058	
Filing Date	March 24, 2004	
Group Art Unit	2818	
Examiner Name	Unknown	
Confirmation No.	4217	
Attorney Docket No.	400.288USO	
Title: MEMORY DEVICE WITH HIGH DIELECTRIC CONSTANT GATE DIELECTRICS AND METAL FLOATING GATES		Sheet 1 of 1

U.S. Patent References				
Examiner Initials	Document No.	Issue/Publication Date	Name	Filing Date
	20020055230	05/09/2002	Chang	11/27/2001
	20020086548	07/04/2002	Chang	12/14/2000
	20030032224	02/13/2003	Sung et al.	08/13/2001
	20030183870	10/02/2003	Sugiyama	02/12/2003
	20030211690	11/13/2003	Chung	05/13/2002
	20040043622	03/04/2004	Chen	09/04/2002
	6,514,831	02/04/2003	Liu	11/14/2001
	6,599,801	07/29/2003	Chang et al.	06/25/2002
	6,784,483	08/31/2004	Chen	09/04/2002
	6,830,963	12/14/2004	Forbes	10/09/2003
	6,838,869	01/04/2005	Rogers et al.	04/02/2001

Foreign Patent References					
Examiner Initials	Foreign Patent		Name	Publication Date	Translation
	Country	No.			

Other References	
Examiner Initials	Author, Title, Date, Pages, etc.
	Min She et al., <i>19th IEEE Non-Volatile Semiconductor Memory Workshop 2003</i> , p. 53-55, "Improved SONOS-type Flash Memory Using HfO ₂ as Trapping Layer"
	Shin et al., <i>19th IEEE Non-Volatile Semiconductor Memory Workshop 2003</i> , p. 58-59, "High Reliable SONOS-type NAND Flash Memory Cell with Al ₂ O ₃ for Top Oxide"
	Blomme et al., <i>19th IEEE Non-Volatile Semiconductor Memory Workshop 2003</i> , p. 93-94, "A Novel Low Voltage Memory Device with an Engineered SiO ₂ /high-k tunneling barrier"
	Lusky et al., (November) 2001, <i>IEEE Electron Device Letters</i> , Volume 22, No. 11, p. 556-558, "Characterization of Channel Hot Electron Injection by the Subthreshold Slope..."

Examiner Signature		Date Considered	
<p>*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>			